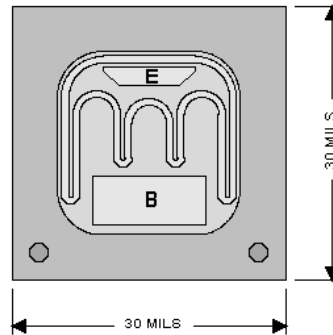


Chip Type 2C3019
Geometry 4500
Polarity PNP

Generic Packaged Parts:
2N3019, 2N3057



[Request Quotation](#)

Chip type **2C3019** by Semicoa Semiconductors provides performance similar to these devices.

Part Numbers:

[2N3019](#), [2N3019S](#), [2N3019UB](#), [2N3057](#), [2N3057A](#),
[2N3700](#), [2N3700UB](#), [SD3019F](#), [SQ3019](#), [SQ3019F](#)

Product Summary:

APPLICATIONS: Designed for general purpose switching and amplifier applications.

Features: [Radiation graphs available](#)

| Mechanical Specifications | | |
|---------------------------|-------------------|----------------------|
| Metallization | Top | Al - 12 kÅ min. |
| | Backside | Au - 6.5 kÅ nom. |
| Bonding Pad Size | Emitter | 2.3 mils x 7.0 mils |
| | Base | 5.0 mils x 11.0 mils |
| Die Thickness | 8 mils nominal | |
| Chip Area | 30 mils x 30 mils | |
| Top Surface | Silox Passivated | |

| Electrical Characteristics | | | | |
|----------------------------|---|-----|-----|------|
| $T_A = 25^\circ\text{C}$ | | | | |
| Parameter | Test conditions | Min | Max | Unit |
| BV_{CBO} | $I_C = 100 \mu\text{A}$, $I_E = 0$ | 140 | --- | V dc |
| BV_{EBO} | $I_E = 100 \mu\text{A}$, $I_C = 0$ | 7.0 | --- | V dc |
| I_{CBO} | $V_{CB} = 40 \text{ V}$, $I_E = 0$ | --- | 10 | nA |
| h_{FE} | $I_C = 150 \text{ mA dc}$, $V_{CE} = 10 \text{ V}$ | 100 | 300 | --- |

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.